Abstracts

Microwave Characteristics of MBE Grown Resonant Tunneling Devices

J.M. Owens, D.J. Halchin, K.L. Lear, W.S. Lee and J.S. Harris, Jr.. "Microwave Characteristics of MBE Grown Resonant Tunneling Devices." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 471-474.

Resonant tunnel beam epitaxy experimentally devices grown by molecular have been measured using network analysis techniques from 130 MHz - 20 GHz. A circuit model for the devices has been extracted for two different InGaAs well structures at a fixed bias point, which fits the measured data well and is useful for circuit design. Additionally, the device impedance has been measured as a function of bias at a fixed frequency point. Complicated capacitance characteristics were observed for the devices with large indium content wells.

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